

IN THE CLAIMS

Please amend the claims as follows:

1-15. (Canceled)

16. (Previously Presented) An optical sensor diode, comprising:

a semiconductor layer including a p region to which p-type impurities are injected, an n region to which n-type impurities are injected, and an i region with a lower impurity concentration than those of the p and n regions;

an anode electrode connected to the p region;

a cathode electrode connected to the n region;

a gate electrode provided above the i region with an insulating film interposed therebetween;

a first electrostatic capacity element formed between the gate electrode and the anode electrode; and

a second electrostatic capacity element formed between the gate electrode and the cathode electrode,

wherein the first electrostatic capacity element is formed of a polysilicon film in the same layer as the semiconductor layer and an upper electrode common to the gate electrode, which is provided so as to overlap the polysilicon film; and

the second electrostatic capacity element is formed of a polysilicon film in the same layer as the semiconductor layer and an upper electrode common to the gate electrode, which is provided so as to overlap the polysilicon film.

17. (Previously Presented) An optical sensor diode, comprising:

a semiconductor layer including a p region to which p-type impurities are injected, an n region to which n-type impurities are injected, and an i region with a lower impurity concentration than those of the p and n regions;

an anode electrode connected to the p region;

a cathode electrode connected to the n region;

a gate electrode provided above the i region with an insulating film interposed therebetween;

a first electrostatic capacity element formed between the gate electrode and the anode electrode; and

a second electrostatic capacity element formed between the gate electrode and the cathode electrode,

wherein the first electrostatic capacity element is formed of a lower electrode common to the gate electrode and a draw-out electrode common to the anode electrode, which is provided so as to overlap the lower electrode; and

the second electrostatic capacity element is formed of a lower electrode common to the gate electrode and a draw-out electrode common to the cathode electrode, which is provided so as to overlap the lower electrode.

18. (Previously Presented) An optical sensor diode, comprising:

a semiconductor layer including a p region to which p-type impurities are injected, an n region to which n-type impurities are injected, and an i region with a lower impurity concentration than those of the p and n regions;

an anode electrode connected to the p region;

a cathode electrode connected to the n region;

a gate electrode provided above the i region with an insulating film interposed therebetween;

a first electrostatic capacity element formed between the gate electrode and the anode electrode; and

a second electrostatic capacity element formed between the gate electrode and the cathode electrode,

wherein the first electrostatic capacity element is formed of the p region and a gate electrode formed so as to overlap the p region, and

the second electrostatic capacity element is formed of the n region and a gate electrode formed so as to overlap the n region.

19. (Previously Presented) An optical sensor diode, comprising:

a semiconductor layer including a p region to which p-type impurities are injected, an n region to which n-type impurities are injected, and an i region with a lower impurity concentration than those of the p and n regions;

an anode electrode connected to the p region;

a cathode electrode connected to the n region;

a gate electrode provided above the i region with an insulating film interposed therebetween;

a first electrostatic capacity element formed between the gate electrode and the anode electrode; and

a second electrostatic capacity element formed between the gate electrode and the cathode electrode,

wherein the first electrostatic capacity element is formed of the gate electrode and an anode electrode formed so as to overlap the gate electrode, and

the second electrostatic capacity element is formed of the gate electrode and a cathode electrode formed so as to overlap the gate electrode.

20. (Original) An image acquisition circuit, comprising:  
a plurality of signal lines installed on a glass insulating substrate;  
a plurality of selective lines installed so as to intersect with the signal lines;  
a common control line installed corresponding to each of the selective lines;  
selection switches provided for the respective signal lines; and  
gate-controlled type optical sensor diodes provided at the respective intersections of the signal lines and the selective lines, in which from an anode electrode and a cathode electrode, one is selected to be connected to the signal line, and the other one is connected to the selective line, and a gate electrode is connected to the common control line.

21. (Original) A method for driving an image acquisition circuit which has a plurality of signal lines installed on a glass insulating substrate, a plurality of selective lines installed so as to intersect with the signal lines, a common control line installed corresponding to each of the selective lines, selection switches provided for the respective signal lines and gate-controlled type optical sensor diodes provided at the respective intersections of the signal lines and the selective lines, in which from an anode electrode and a cathode electrode, one is selected to be connected to the signal line, and the other one is connected to the selective line, and a gate electrode is connected to the common control line, the method comprising the steps of:

applying a fixed voltage to the common control line;  
turning on a selection switch of a signal line to which an optical sensor diode for detecting the amount of light is connected; and

applying a voltage larger than the fixed voltage to a selective line to which the optical sensor diode for detecting the amount of light is connected.